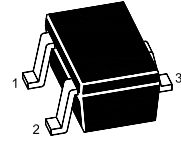
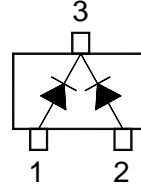


RB715W

Schottky Barrier Diode

Features

- Low current rectification



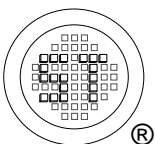
SOT-323 Plastic Package
Marking Code: **3D**

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RM}	40	V
Reverse Voltage	V_R	40	V
Average Rectified Forward Current	$I_{F(AV)}$	30	mA
Peak Forward Surge Current ($t = 8.3\text{ ms}$)	I_{FSM}	200	mA
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

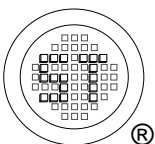
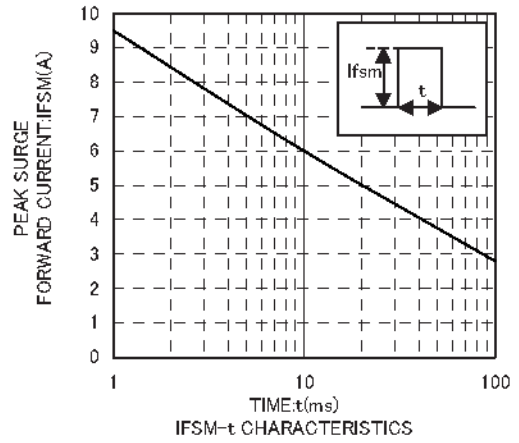
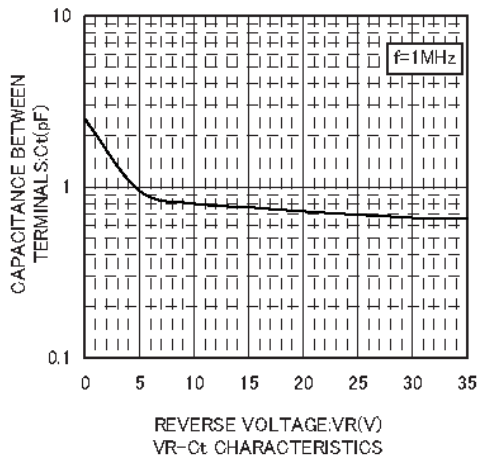
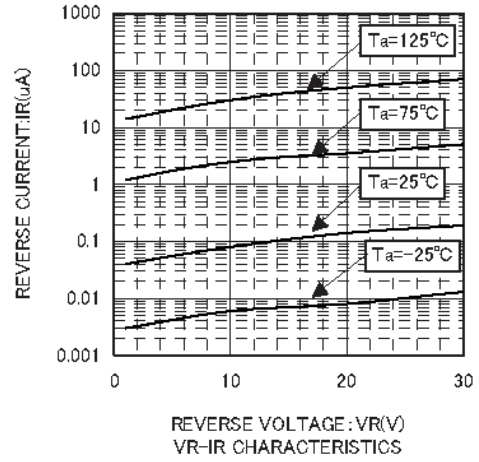
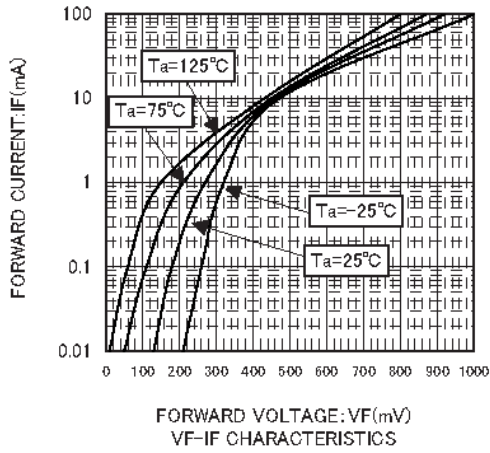
Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$	V_F	-	-	0.37	V
Reverse Breakdown Voltage at $I_R = 10\text{ }\mu\text{A}$	$V_{(BR)R}$	40	-	-	V
Reverse Current at $V_R = 10\text{ V}$	I_R	-	-	1	μA
Capacitance between Terminals at $V_R = 1\text{ V}$, $f = 1\text{ MHz}$	C_t	-	2	-	pF



SEMTECH ELECTRONICS LTD.





SEMTECH ELECTRONICS LTD.



ISO/TS 16949 : 2009
Certificate No. 16073000



ISO14001 : 2004
Certificate No. 7116



ISO 9001 : 2008
Certificate No. 5070410



BS-OHSAS 18001 : 2007
Certificate No. 7116



IECQ QC 080000
Certificate No. PNC-8294-148-1